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CONTENTS

Tuesday, September 1

Opening Session (13 : 30 ~ 13 : 40)

Chairperson : Y. Uraoka, *NAIST, Japan*

Welcome Address

H. Hamada, *Kinki Univ., Japan*

Award Presentation

Session 1 : Keynote Address (13 : 40 ~ 14 : 45)

Chairpersons : Y. Uraoka, *NAIST, Japan*

H. Okada, *Univ. of Toyama, Japan*

- 13 : 45 (1-1) Metal Halide Perovskites for Next-Generation LED and Transistor Applications (Invited).....1
T. Matsushima, C. Adachi, *Kyushu Univ., Japan*
- 14 : 15 (1-2) Advanced PECVD Processes for SiNW Based Solar Cells and Thin Film Transistors
(Invited).....3
P. Roca i Cabarrocas^{1,2}, L. Yu³, ¹*Ecole Polytechnique, France*, ²*IPVVF, France*, ³*Nanjing Univ., China*

— Break —

Session 2 : Advances in Solar Photovoltaic Technologies (14 : 55 ~ 16 : 05)

Chairpersons : Y. Ishikawa, *Aoyama Gakuin Univ., Japan*

T. Kaneko, *Tokai Univ., Japan*

- 15 : 00 (2-1) Vacuum Deposition and Crystal Growth Dynamics of Metal Halide Perovskite (Invited).....4
T. Miyadera, *Nat'l Inst. of Advanced Industrial Sci. and Technol. (AIST), Japan*
- 15 : 25 (2-2) Development of Microwave Induced Rapid Heating System Using Wireless Carbon Heating
Tubes.....7
T. Miyazaki^{1,2}, R. Seki², T. Uehara², T. Arima², M. Hasumi², G. Kobayashi³, I. Serizawa³, T.
Sameshima², ¹*Techno Res., Ltd., Japan*, ²*Tokyo Univ. of Agriculture and Technol., Japan*, ³*ORC
MANUFACTURING Co., Ltd., Japan*
- 15 : 45 (2-3) Inter-Layer Solid-Phase Reaction in Halide Perovskite Fabricated via Alternate Laser
Deposition.....11
N. Matsuki, Y. Iida, Y. Abe, T. Shimada, T. Sato, *Kanagawa Univ., Japan*

Wednesday, September 2

Special Symposium : The Future Vehicle Displays (9 : 25 ~)

Special Symposium 1 : OLED Materials with Breakthrough and Novel Systems for Vehicle Applications (9 : 25 ~ 10 : 30)

Chairpersons : H. Tanabe, *Tianma Japan, Japan*
A. Masuda, *Niigata Univ., Japan*

- 9 : 30 (SS1-1) Phosphorescent OLED Materials with Breakthrough Spectral Line Shape and Operational Stability for Automotive Applications (Invited).....13
E. A. Margulies, P. -L. T. Boudreault, V. I. Adamovich, B. D. Alleyne, M. S. Weaver, J. J. Brown, *Universal Display Corporation, USA*
- 10 : 00 (SS1-2) E-Tint Systems in Automotive Applications (Invited).....17
B. Taheri¹, M. Derr², ¹*AlphaMicron Inc., USA*, ²*Akri, LLC, USA*

— Break —

Special Symposium 2 : Forecast of Display Market (10 : 40 ~ 11 : 15)

Chairpersons : H. Okada, *Univ. of Toyama, Japan*
T. Arai, *JOLED, Japan*

- 10 : 45 (SS2-1) Automotive Display Market Outlook- 2020 (Invited).....19
S. Wu, *Omdia Res., Taiwan*

— Lunch —

Special Symposium 3 : Key Materials and Developments for Vehicle Display Applications (13 : 00 ~ 13 : 35)

Chairpersons : T. Arai, *JOLED, Japan*
H. Okada, *Univ. of Toyama, Japan*

- 13 : 05 (SS3-1) Key Technologies in Solution-Process OLED Materials (Invited).....23
K. Iida, H. Gorohmaru, K. Nagayama, K. Ishibashi, Y. Shoji, K. Okabe, *Mitsubishi Chemical Corp., Japan*

— Break —

Special Symposium 4 : Newly Design and Approach in Vehicle Display (14 : 15 ~ 15 : 50)

Chairpersons : M. Kimura, *Ryukoku Univ., Japan*
Y. Uraoka, *NAIST, Japan*

- 14 : 20 (SS4-1) Newly-Designed Pixel Circuit and Reflector Cavity with LTPS TFT for MicroLED Display (Invited).....27
H. Ito¹, M. Tamaki¹, T. Suzuki¹, K. Aoki¹, R. Yokoyama¹, S. Nakamitsu¹, K. Imaizumi¹, K. Yamanoguchi¹, M. Nishide¹, F. Rahadian¹, S. Matsuda¹, E. Lang², L. Hoeppel², ¹*Kyocera Corp., Japan*, ²*OSRAM Opto Semiconductors GmbH, Germany*
- 14 : 50 (SS4-2) Development of 12.3-inch Highly Transparent Color LCD by Scattering Mode with Direct Edge Light and Field Sequential Driving Method (Invited).....31
T. Nakamura, Y. Omori, M. Miyao, K. Kitamura, H. Sugiyama, Y. Oue, K. Yamaguchi, T. Maeta, S. Kajikawa, M. Yukawa, T. Imai, S. Ishida, K. Okuyama, *Japan Display Inc., Japan*
- 15 : 20 (SS4-3) 30-Inch 4K Rollable AM-OLED Display (Invited).....35
T. Sonoda¹, S. Murashige¹, K. Tanaka¹, Kenji Takase¹, H.i Katoh¹, Y. Kataoka¹, T. Usui², T. Okada², T. Shimizu², ¹*Sharp Corp., Japan*, ²*NHK Sci. & Technol. Res. Labs., Japan*

— Break —

Special Symposium 5 : Concepts and Trends for Future Vehicle Display Applications

(16 : 00 ~ 16 : 35)

Chairpersons : H. Okada, *Univ. of Toyama, Japan*
T. Arai, *JOLED, Japan*

- 16 : 05 (SS5-1) User Experience and HMI Technologies for the Future (Invited).....39
D. S. Hermann, S. Singh, *Volvo Cars., Sweden*

— Break —

Panel Discussion (16: 45 ~)

Thursday, September 3

Symposium 1 : Emerging Technologies for Ubiquitous Electric Power Generation by [PV + X]

(9 : 25 ~ 11 : 00)

Chairpersons : N. Matsuki, *Kanagawa Univ., Japan*

A. Wakamiya, *Kyoto Univ., Japan*

- 9 : 30 (S1-1) Sensitized "Thermal" Cell: A New Heat Conversion System to Electricity (Invited).....45
S. Matsushita, *Tokyo Inst. of Technol., Japan*
- 10 : 00 (S1-2) Air-Stable n-Type Organic Semiconductors for Thermoelectric Generators (Invited).....48
M. Murata^{1,2}, ¹*Osaka Inst. of Technol., Japan*, ²*JST-PRESTO, Japan*
- 10 : 30 (S1-3) Pb- and Sn- Based Perovskite Solar Cells Based on Highly Purified Materials (Invited).....N/A
A. Wakamiya, *Kyoto Univ., Japan*

— Break —

Symposium 2 : Oxide TFT Technologies for New Applications (11 : 10 ~ 12 : 15)

Chairpersons : M. Kitamura, *Kobe Univ., Japan*

N. Saito, *Kioxia, Japan*

- 11 : 15 (S2-1) IGZO Channel Ferroelectric Memory FET (Invited).....51
M. Kobayashi, *Univ. of Tokyo, Japan*
- 11 : 45 (S2-2) Low-Temperature-Operated Sensitive NO₂ Gas Sensors Based on P-Type SnO Thin-Film
and Thin-Film Transistors (Invited).....55
H. -I. Kwon, *Chung-Ang Univ., Korea*

— Lunch —

Symposium 3 : Recent Progress in Thin-Film Device Fabrication (13 : 45 ~ 15 : 20)

Chairpersons : H. Kajii, *Osaka Univ, Japan*
A. Heya, *Univ. of Hyogo, Japan*

- 13 : 50 (S3-1) Semiconductive Single Molecular Bilayers: a New Platform for High-Performance Organic Transistors (Invited).....63
S. Arai, *Univ. of Tokyo, Japan*
- 14 : 20 (S3-2) Orientation of Semiconducting Polymers via Swift Printing and Drawing Techniques for High Performance Organic Electronic Devices (Invited).....67
N. Kumari, S. Sharma, S. Nagamatsu, S. S. Pandey, *Kyushu Inst. of Technol., Japan*
- 14 : 50 (S3-3) Enhanced Eu Luminescence in GaN:Eu, O-Based Light Emitting Diodes via Introduction of Nanostructures and Nanocavities (Invited).....71
J. Tatebayashi, S. Ichikawa, Y. Fujiwara, *Osaka Univ., Japan*

Poster Session (15 : 40 ~ 17 : 40)

Chairpersons :

TFMDp

- (P-1) Deuteration of Pentacene Using Deuterium Gas and Heated Catalyst.....73
A. Heya¹, R. Yamasaki², K. Sumitomo¹, ¹*Univ. of Hyogo., Japan*, ²*Tocalo Co., Ltd., Japan*
- (P-2) Improved Carrier Mobility of Sn-Doped Ge Thin-Films (≤ 50 nm) by Interface-Modulated Solid-Phase Crystallization Combined with Thinning.....75
M. Chiyozone, X. Gong, T. Sadoh, *Kyushu Univ., Japan*
- (P-3) Ga-Sn-O Thin Film Synapse for Neuromorphic Device.....77
Y. Shibayama¹, Y. Ohnishi¹, D. Yamakawa¹, H. Yamane², Y. Nakashima², M. Kimura^{1,2},
¹*Ryukoku Univ., Japan*, ²*Nara Inst. of Sci. and Technol. (NAIST), Japan*
- (P-4) Relationship of Phase Shift Mask Design and Size of Three-Dimension Nanostructures.....80
P. Sihapitak¹, Y. Ishikawa^{1,2}, X. Wang¹, M. Uenuma¹, Y. Uraoka¹, ¹*Nara Inst. of Sci. and Technol. (NAIST), Japan*, ²*Aoyama Gakuin Univ., Japan*
- (P-5) Mechanism Study on Deposition of SiO_x Films Produced by Silicone Oil and Ozone Gas.....83
W. Zhou, S. Horita, *Japan Advanced Inst. Sci. and Technol. (JAIST), Japan*
- (P-6) Study on Perovskite Photo-Sensors with Solution-Processed Compact TiO₂ Under Low Temperature Fabrication Process.....87
I. Hirano, R. Takano, C. Zhang, H. Okada, *Univ. of Toyama, Japan*
- (P-7) Withdrawn
- (P-8) Deposition Condition at Low Temperature for Crystallization Enhancement of YSZ Films on Glass Substrates by Reactive Sputtering.....89
J. Patidar, S. Horita, *Japan Advanced Inst. Sci. and Technol. (JAIST), Japan*
- (P-9) Evaluations of Selective Dry Etching of GaAs Core Layer Having Embedded InAs Quantum Dots Using Optical Measurements towards Photonic Crystal Laser Fabrication.....93
T. Okunaga¹, T. Nozue¹, Y. Xiong¹, H. Kajii¹, M. Morifuji¹, J. Tatebayashi¹, Y. Fujiwara¹, T. Nishihashi², M. Kondow¹, ¹*Osaka Univ., Japan*, ²*ULVAC, Inc., Japan*
- (P-10) Mechanochromic Behavior of Side-Chain Spiropyran Polymer Films.....97
S. Hirooka, M. Kondo, K. Yoshiki, N. Kawatsuki, *Univ. of Hyogo, Japan*
- (P-11) SiSn Film on Insulator by Low-Temperature Solid-Phase Crystallization.....99
T. Kosugi, K. Yagi, T. Sadoh, *Kyushu Univ., Japan*
- (P-12) Evaluation of Thermoelectric Properties of Ga-Sn-O Thin Film Formed by Mist CVD Method.....101
T. Aramaki¹, T. Matsuda¹, Y. Ikeguchi², M. Uenuma², M. Kimura¹, ¹*Ryukoku Univ., Japan*, ²*Nara Inst. of Sci. and Technol. (NAIST), Japan*

FPDp (P-13)	Withdrawn
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(P-14)	Withdrawn
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TFTp (P-15)	Withdrawn
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Friday, September 4

Session 3 : New Proposals in Drive Circuit for FPD (9 : 25 ~ 10 : 30)

Chairpersons : R. Hattori, *Kyushu Univ., Japan*
T. Mori, *Aichi Inst. of Technol., Japan*

- 9 : 30 (3-1) Withdrawn
- 9 : 50 (3-2) Compensation Pixel Circuit Based on LTPS TFTs to Improve Effect of Leakage Current for AMOLED Displays with Low Frame Rate.....107
P. -T. Lee, Y. -S. Lin, C. -L. Lin, *Nat'l Cheng Kung Univ., Taiwan*
- 10 : 10 (3-3) Simplified Compensation Circuit Using Simultaneous Emission Driving Method for Highresolution AMOLED Displays.....111
C. -L. Tsai, J. -H. Chang, C. -L. Lin, *Nat'l Cheng Kung Univ., Taiwan*

— Break —

Session 4 : Novel Fabrication Processing and Applications (10 : 40 ~ 11 : 50)

Chairpersons : A. Heya, *Univ. of Hyogo, Japan*
H. Kajii, *Osaka Univ., Japan*

- 10 : 45 (4-1) Wearable Sensors Corresponding to Various Applications in Medical/Healthcare Field (Invited).....115
K. Miyamoto, K. Hashimoto, M. Kasaoka, M. Kakumu, *TDK Corp., Japan*
- 11 : 10 (4-2) Characteristics of Noble-Gas-Ion-Implanted Amorphous-InGaZnO Films on Glass.....119
T. Ui¹, R. Fujimoto¹, T. Sakai², D. Matsuo², Y. Setoguchi², Y. Andoh², J. Tatemichi¹, ¹*KNISSIN ION EQUIPMENT CO., LTD., Japan*, ²*NISSIN ELECTRIC CO., LTD., Japan*
- 11 : 30 (4-3) Fabrication and Characterization of Ba_{1/3}CoO₂ Epitaxial Films Exhibiting Thermoelectric ZT = 0.12 at Room Temperature.....123
Y. Takashima¹, Y. -Q. Zhang¹, J. Wei^{2,3}, B. Feng², Y. Ikuhara^{2,3}, H. J. Cho¹, H. Ohta¹, ¹*Hokkaido Univ., Japan*, ²*The Univ. of Tokyo, Japan*, ³*Kyoto Univ., Japan*

— Lunch —

Session 5 : Advance in Oxide TFTs (13 : 00 ~ 14 : 10)

Chairpersons : S. Horita, *JAIST, Japan*

N. Saito, *Kioxia, Japan*

- 13 : 05 (5-1) Electronic Defects in Amorphous Oxide Semiconductor and Recent Development (Invited).....127
K. Ide, H. Hosono, T. Kamiya, *Tokyo Inst. of Technol., Japan*
- 13 : 30 (5-2) Photo-Assisted Processing of Amorphous Gallium Oxide (a-GaO_x) Thin Film for Flexible and
Transparent Device Application.....131
D. Purnawati, J. P. Bermundo, Y. Ishikawa, Y. Uraoka, *Nara Inst. of Sci. and Technol. (NAIST),
Japan*
- 13 : 50 (5-3) Fabrication and Operating Mechanism of Deep-UV Transparent Semiconducting SrSnO₃-Based Thin
Film Transistor.....133
L. Gong^{1,2}, M. Wei^{1,2}, D.-D. Liang^{1,2}, H. J. Cho², H. Ohta², ¹*Univ. of , Sci. and Technol. Beijing,
China*, ²*Hokkaido Univ., Japan*

— Break —

Session 6 : Characterization and Applications of TFTs (14 : 20 ~ 15 : 30)

Chairpersons : M. Kimura, *Ryukoku Univ., Japan*

M. Kitamura, *Kobe Univ., Japan*

- 14 : 25 (6-1) Device Modeling of Oxide Semiconductor TFTs (Invited).....137
K. Abe, K. Ota, T. Kuwagaki, *Silvaco Japan Co., Ltd., Japan*
- 14 : 50 (6-2) Comparison of Pixel Circuits in Pig Eyeball Experiment of Artificial Retina Using Thin-Film
Devices.....141
K. Toyoda¹, K. Tomioka¹, K. Misawa¹, N. Naitou¹, T. Noda², J. Ohta³, M. Kimura¹, ¹*Ryukoku
Univ., Japan*, ²*Toyohashi Univ. of Technol., Japan*, ³*Nara Inst. of Sci. and Technol. (NAIST),
Japan*
- 15 : 10 (6-3) Withdrawn

Closing Remarks (15 : 30 ~ 15 : 40)